# Yingxin Guan

## List of Publications by Year in descending order

Source: https://exaly.com/author-pdf/2668958/publications.pdf

Version: 2024-02-01

| | | | |
|---|---|---|---|
| 21 papers | 307 citations | 1040056 9 h-index | 839539 18 g-index |
| 21 all docs | 21 docs citations | 21 times ranked | 572 citing authors |

| # | Article | IF | Citations |
|---|---|---|---|
| 1 | Thermodynamic stability analysis of Bi-containing III-V quaternary alloys and the effect of epitaxial strain. Journal of Physics and Chemistry of Solids, 2020, 138, 109245. | 4.0 | 6 |
| 2 | Reduction of Interface Reactions in the Low-Temperature Solid-Phase Epitaxy of ScAlMgO4 on Al2O3(0001). Crystal Growth and Design, 2020, 20, 6001-6007. | 3.0 | 2 |
| 3 | Metal-organic vapor phase epitaxy of the quaternary metastable alloy In1â€“xGaxAs1â^'yBiy and its kinetics of growth. Journal of Crystal Growth, 2020, 538, 125611. | 1.5 | 0 |
| 4 | High-Ge-Content SiGe Alloy Single Crystals Using the Nanomembrane Platform. ACS Applied Materials & Interfaces, 2020, 12, 20859-20866. | 8.0 | 7 |
| 5 | Radiation-induced segregation in a ceramic. Nature Materials, 2020, 19, 992-998. | 27.5 | 47 |
| 6 | Highly tin doped GaAs at low growth temperatures using tetraethyl tin by metal organic vapor phase epitaxy. Journal of Crystal Growth, 2019, 507, 255-259. | 1.5 | 3 |
| 7 | Impact of thermal annealing on internal device parameters of GaAs <sub>0.965</sub> Bi <sub>0.035</sub> /GaAs <sub>0.75</sub> P <sub>0.25</sub> quantum well lasers. IET Optoelectronics, 2019, 13, 12-16. | 3.3 | 4 |
| 8 | Characteristics of OMVPE grown GaAsBi QW lasers and impact of post-growth thermal annealing. Journal of Applied Physics, 2018, 123, . | 2.5 | 13 |
| 9 | Single junction solar cell employing strain compensated GaAs0.965Bi0.035/GaAs0.75P0.25 multiple quantum wells grown by metal organic vapor phase epitaxy. Applied Physics Letters, 2018, 112, . | 3.3 | 5 |
| 10 | Surface kinetics study of metal-organic vapor phase epitaxy of GaAs 1â^'y Bi y on offcut and mesa-patterned GaAs substrates. Journal of Crystal Growth, 2017, 464, 39-48. | 1.5 | 4 |
| 11 | Annealing-induced precipitate formation behavior in MOVPE-grown GaAs<sub>1â^'x</sub>Bi<sub>x</sub>explored by atom probe tomography and HAADF-STEM. Nanotechnology, 2017, 28, 215704. | 2.6 | 14 |
| 12 | Distinct Nucleation and Growth Kinetics of Amorphous SrTiO<sub>3</sub> on (001) SrTiO<sub>3</sub> and SiO<sub>2</sub>/Si: A Step toward New Architectures. ACS Applied Materials & Interfaces, 2017, 9, 41034-41042. | 8.0 | 17 |
| 13 | Atomic Layer Deposition of Al<sub>2</sub>O<sub>3</sub>â€“Ga<sub>2</sub>O<sub>3</sub> Alloy Coatings for Li[Ni<sub>0.5</sub>Mn<sub>0.3</sub>Co<sub>0.2</sub>]O<sub>2</sub> Cathode to Improve Rate Performance in Li-Ion Battery. ACS Applied Materials & Interfaces, 2016, 8, 10572-10580. | 8.0 | 51 |
| 14 | Atom probe tomography evidence for uniform incorporation of Bi across the growth front in GaAs1â^'Bi /GaAs superlattice. Journal of Crystal Growth, 2016, 446, 27-32. | 1.5 | 5 |
| 15 | Enhanced Incorporation of P into Tensile-Strained GaAs1-yPyLayers Grown by Metal-Organic Vapor Phase Epitaxy at Very Low Temperatures. ECS Journal of Solid State Science and Technology, 2016, 5, P183-P189. | 1.8 | 3 |
| 16 | The Effect of the Bi Precursors, (CH<sub>3</sub>)<sub>3</sub>Bi and (C<sub>2</sub>H<sub>5</sub>)<sub>3</sub>Bi, on the Metalâ€Organic Vapor Phase Epitaxy of GaAs<sub>1â€‹y</sub>Bi<sub>y</sub> Films. Chemical Vapor Deposition, 2015, 21, 166-175. | 1.3 | 15 |
| 17 | Enhanced Activity and Stability of TiO<sub>2</sub>-Coated Cobalt/Carbon Catalysts for Electrochemical Water Oxidation. ACS Catalysis, 2015, 5, 3463-3469. | 11.2 | 48 |
| 18 | GaAs1â^'yâ^'zPyBiz, an alternative reduced band gap alloy system lattice-matched to GaAs. Applied Physics Letters, 2014, 105, . | 3.3 | 23 |

| # | Article | IF | Citations |
|---|---|---|---|
| 19 | Unexpected Bismuth Concentration Profiles in MOVPE GaAs1-xBix Films Revealed by HAADF STEM Imaging. Microscopy and Microanalysis, 2014, 20, 196-197. | 0.4 | 0 |
| 20 | Tungsten hexacarbonyl and hydrogen peroxide as precursors for the growth of tungsten oxide thin films on titania nanoparticles. AICHE Journal, 2014, 60, 1278-1286. | 3.6 | 9 |
| 21 | Self-limiting growth when using trimethyl bismuth (TMBi) in the metal-organic vapor phase epitaxy (MOVPE) of GaAs1â^'yBiy. Journal of Crystal Growth, 2014, 395, 38-45. | 1.5 | 31 |